

Ref #	Hits	Search Query	DBs	Default Operator	Plurals	Time Stamp
L1	937	high near density near5 rom	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/07/22 16:37
L2	39	(high near density near5 rom) and (heavily near doped)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/07/22 16:37
L3	7	(high near density near5 rom) and (heavily near doped) and diode	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/07/22 16:37
L4	2	(high near density near5 rom) and (heavily near doped) and diode. clm.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/07/22 16:38
L5	1455	(doped near5 region near5 diode)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/07/22 16:39
L6	352	(doped near5 region near5 diode). clm.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/07/22 16:39
L7	4	rom.clm. and (doped near5 region near5 diode).clm.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/07/22 16:40
L8	3	rom.clm. and (doped near5 region near5 diode near5 (form or forming or formed or formation)). clm.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/07/22 16:40
L9	6	rom.clm. and (doped near5 region near5 diode near5 (form or forming or formed or formation))	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/07/22 16:40

L10	27	rom and (doped near5 region near5 diode near5 (form or forming or formed or formation))	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/07/22 16:41
L11	4	rom and (doped near5 region near5 diode near5 (form or forming or formed or formation) near5 (source or drain or source/drain))	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/07/22 16:41
L12	8	rom and (doped near10 region near10 diode near10 (form or forming or formed or formation) near10 (source or drain or source/drain) near10 (heavily or lightly))	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/07/22 16:42
L13	3	rom.clm. and (doped near10 region near10 diode near10 (form or forming or formed or formation) near10 (source or drain or source/drain) near10 (heavily or lightly))	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/07/22 16:43
L14	3	rom.clm. and (doped near10 region near10 diode near10 (form or forming or formed or formation) near10 (source or drain or source/drain) near10 ((heavily or lightly) near doped))	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/07/22 16:43
L15	8	rom and (doped near10 region near10 diode near10 (form or forming or formed or formation) near10 (source or drain or source/drain) near10 ((heavily or lightly) near doped))	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/07/22 16:43
L16	5	rom and (doped near10 region near10 diode near10 (form or forming or formed or formation) near10 (source or drain or source/drain) near10 ((heavily) near doped))	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/07/22 19:16
L17	3616	(rom same diode)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/07/22 19:17
L18	3	(rom same (heavily adj doped) with diode)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/07/22 19:17

L19	6	(rom same (heavily adj doped) same diode)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/07/22 19:18
L20	34	(rom same (p+ or n+ or (heavily adj doped)) same diode)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/07/22 19:18
L21	7	(rom same (p+ or n+ or (heavily adj doped)) same (source or drain or source/drain) same diode)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/07/22 19:19
L22	4	(rom same (p+ or n+ or (heavily adj doped)) same (source or drain or source/drain) same ((create or creating or created or form or formed or forming) near5 diode))	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/07/22 19:20
L23	3	(rom with (p+ or n+ or (heavily adj doped)) same (source or drain or source/drain) same ((create or creating or created or form or formed or forming) near5 diode))	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/07/22 19:20
L24	3	(rom with (p+ or n+ or (heavily adj doped)) same (source or drain or source/drain) with ((create or creating or created or form or formed or forming) near5 diode))	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/07/22 19:21
L25	1	(rom with (p+ or n+ or (heavily adj doped)) same (source or drain or source/drain) with ((create or creating or created or form or formed or forming) near5 diode)). clm.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/07/22 19:21
L26	1	((memory or rom) with (p+ or n+ or (heavily adj doped)) same (source or drain or source/drain) with ((create or creating or created or form or formed or forming) near5 diode)).clm.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/07/22 19:22
L27	9	((memory or rom) with (p+ or n+ or (heavily adj doped)) same (source or drain or source/drain) with ((create or creating or created or form or formed or forming) near5 diode))	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/07/22 19:22

L28	5	((memory or rom) with (p+ or n+ or (heavily adj doped)) with (source or drain or source/drain) with ((create or creating or created or form or formed or forming) near5 diode))	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/07/22 19:22
L29	13	((memory or rom) same (p+ or n+ or (heavily adj doped)) with (source or drain or source/drain) with ((create or creating or created or form or formed or forming) near5 diode))	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/07/22 19:22
L30	17	((memory or rom) same (p+ or n+ or (heavily adj doped)) same (source or drain or source/drain) with ((create or creating or created or form or formed or forming) near5 diode))	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/07/22 19:22
L31	43	((memory or rom) same (p+ or n+ or (heavily adj doped)) same (source or drain or source/drain) same ((create or creating or created or form or formed or forming) near5 diode))	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/07/22 19:23
L32	1	((memory or rom) same (p+ or n+ or (heavily adj doped)) same (source or drain or source/drain) same ((create or creating or created or form or formed or forming) near5 diode)).clm.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/07/22 19:23
L33	9	((memory or rom) same (p+ or n+ or (heavily adj doped)) same (source or drain or source/drain) same ((create or creating or created or form or formed or forming) near5 diode)).ti,ab,clm.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/07/22 19:24
L34	25	((memory or rom) same (p+ or n+ or (heavily adj doped)) same (source or drain or source/drain) same ((create or creating or created or form or formed or forming) near2 diode))	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/07/22 19:25
L35	14	((memory or rom) same (p+ or n+ or (heavily adj doped)) same (source or drain or source/drain) same ((create or creating or created or form or formed or forming) near2 diode)) and diode. clm.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/07/22 19:26

L36	13	((memory or rom) same (p+ or n+ or (heavily adj doped)) same (source or drain or source/drain) same ((create or creating or created or form or formed or forming) near2 diode)) and ((create or creating or created or creation or form or forming or formed or formation) near5 diode).clm.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/07/22 19:27
L37	6	((memory or rom) same (p+ or n+ or (heavily adj doped)) same (source or drain or source/drain) same ((create or creating or created or form or formed or forming) near2 diode)) and ((create or creating or created or creation or form or forming or formed or formation) near5 diode near5 (source or drain or source/drain)).clm.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/07/22 19:28
L38	1	((memory or rom) same (p+ or n+ or (heavily adj doped)) same (source or drain or source/drain) same ((create or creating or created or form or formed or forming) near2 diode)) and ((create or creating or created or creation or form or forming or formed or formation) near5 diode near5 (source or drain or source/drain) near5 (heavily or p+ or n+ or doped)).clm.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/07/22 19:28
L39	13	((create or creating or created or creation or form or forming or formed or formation) near5 diode near5 (source or drain or source/drain) near5 (heavily or p+ or n+ or doped)).clm.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/07/22 19:29
L40	1	((create or creating or created or creation or form or forming or formed or formation) near5 diode near5 (source or drain or source/drain) near5 (heavily or p+ or n+ or doped)).clm. and rom. clm.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/07/22 19:29
L41	2	((create or creating or created or creation or form or forming or formed or formation) near5 diode near5 (source or drain or source/drain) near5 (heavily or p+ or n+ or doped)).clm. and (memory or rom).clm.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/07/22 19:29



L42	6795	(rom or memory).clm. and diode. clm.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/07/22 19:29
L43	142	(rom or memory).clm. and ((doped or doping or dope or n+ or p+) near5 diode).clm.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/07/22 19:30
L44	64	(rom or memory).clm. with ((doped or doping or dope or n+ or p+) near5 diode).clm.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/07/22 19:30
L45	27	(rom or memory).clm. with ((doped or doping or dope or n+ or p+) near5 ((form or forming or formed or formation or create or created or creation) near5 diode)). clm.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/07/22 19:31
L46	22	(rom or memory).clm. with ((doped or doping or dope or n+ or p+) near5 ((form or forming or formed or formation or create or created or creation) near2 diode)). clm.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/07/22 19:31
L47	2	(rom).clm. with ((doped or doping or dope or n+ or p+) near5 ((form or forming or formed or formation or create or created or creation) near2 diode)).clm.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/07/22 19:34
L48	3	(rom).clm. and ((doped or doping or dope or n+ or p+) near5 ((form or forming or formed or formation or create or created or creation) near2 diode)).clm.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/07/22 19:35
L49	62	(rom or memory).clm. and ((doped or doping or dope or n+ or p+) near5 ((form or forming or formed or formation or create or created or creation) near2 diode)). clm.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/07/22 19:35
L50	23	(rom or memory).clm. and ((doped or doping or dope or n+ or p+) near5 ((form or forming or formed or formation or create or created or creation) near2 diode)). clm. and (high adj density)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/07/22 19:35

L51	1	(rom or memory).clm. and ((doped or doping or dope or n+ or p+) near5 ((form or forming or formed or formation or create or created or creation) near2 diode)).clm. and (high adj density).clm.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/07/22 19:35
L52	7	(high near density near rom).clm.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/07/22 19:35
L53	1	(high near density near rom).clm. and diode.clm.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/07/22 19:36
L54	6	(high near density near (memory or rom)).clm. and diode.clm.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/07/22 19:36
L55	16	(high near density near5 (memory or rom)).clm. and diode.clm.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/07/22 19:36
L56	2	(high near density near5 (memory or rom)).clm. and ((doped or dope or doping or n+ or p+) near5 diode).clm.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/07/22 19:37
L57	2	(high near density near5 (memory or rom)).clm. and ((doped or dope or doping or n+ or p+) near10 diode).clm.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/07/22 19:37
L58	2	(high near density near5 (memory or rom)).clm. and ((doped or dope or doping or n+ or p+) with diode).clm.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/07/22 19:37
L59	8	(rom).clm. and ((doped or dope or doping or n+ or p+) with diode).clm.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/07/22 19:38
L60	2	(rom).clm. with ((doped or dope or doping or n+ or p+) with diode).clm.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/07/22 19:38